



#### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
40V	1.2m $\Omega$ @10V	250A

#### Feature

- Split Gate Trench Technology
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

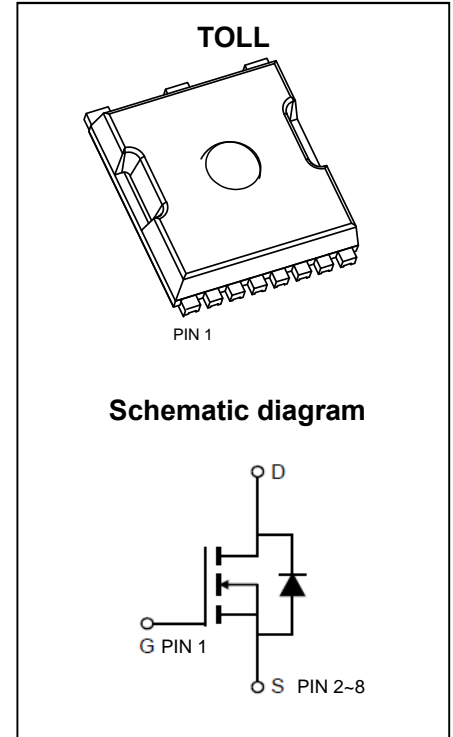
#### Application

- Power Switching Application

#### MARKING:



T010N04L = Device Code  
XX = Date Code  
Solid Dot = Green Indicator



#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain - Source Voltage	$V_{DS}$	40	V
Gate - Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current <sup>1</sup>	$T_C = 25^\circ\text{C}$	$I_D$	250 A
	$T_C = 100^\circ\text{C}$	$I_D$	163 A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	1000	A
Single Pulsed Avalanche Current <sup>3</sup>	$I_{AS}$	72	A
Single Pulsed Avalanche Energy <sup>3</sup>	$E_{AS}$	669	mJ
Power Dissipation <sup>5</sup>	$T_C = 25^\circ\text{C}$	$P_D$	250 W
Thermal Resistance from Junction to Ambient <sup>6</sup>	$R_{\theta JA}$	45	$^\circ\text{C}/\text{W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.5	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$

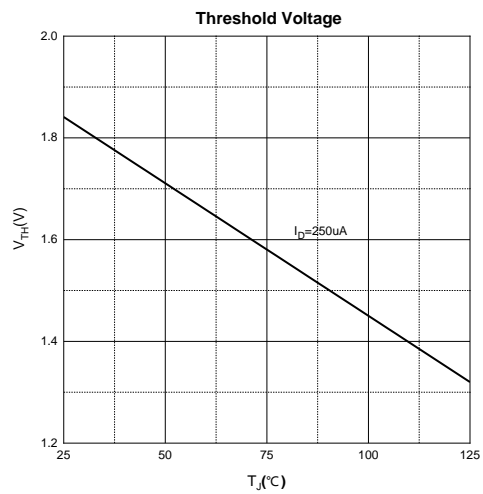
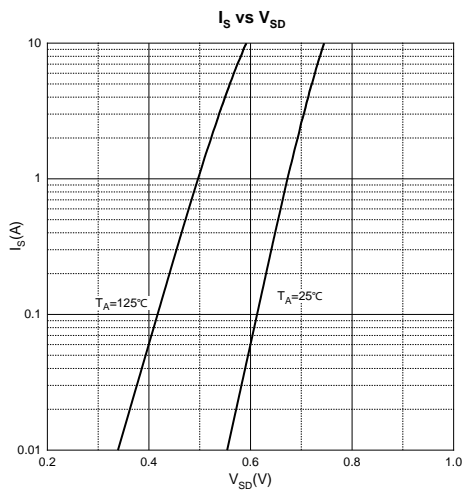
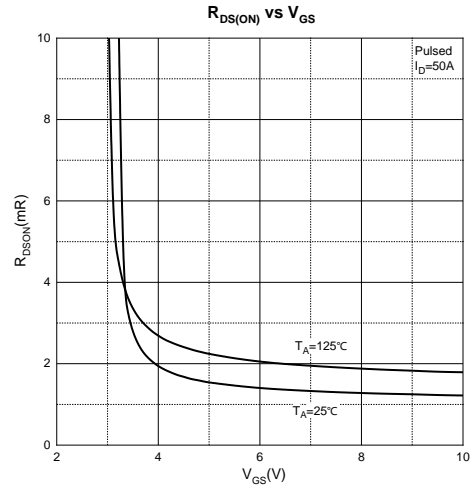
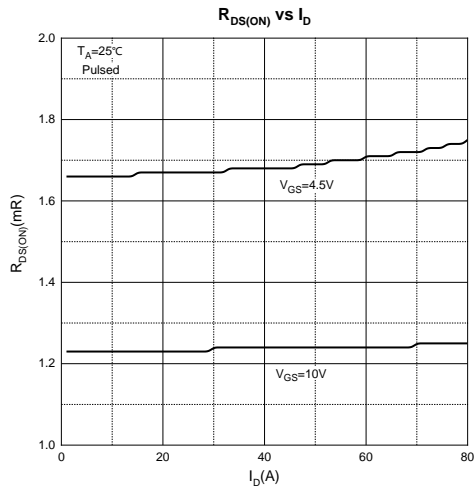
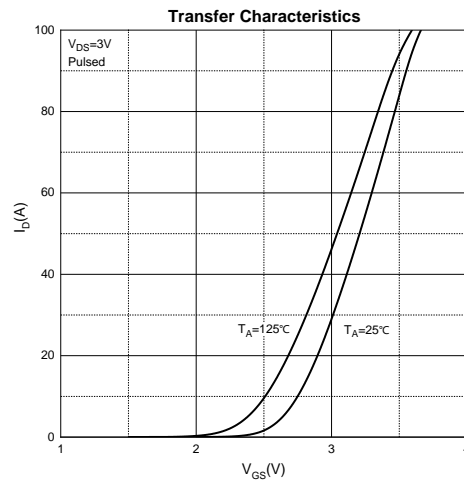
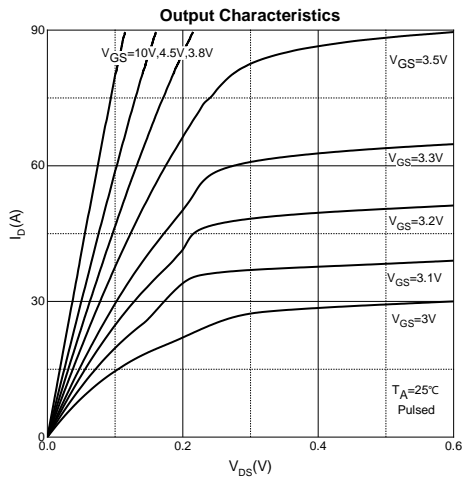
**MOSFET ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)**

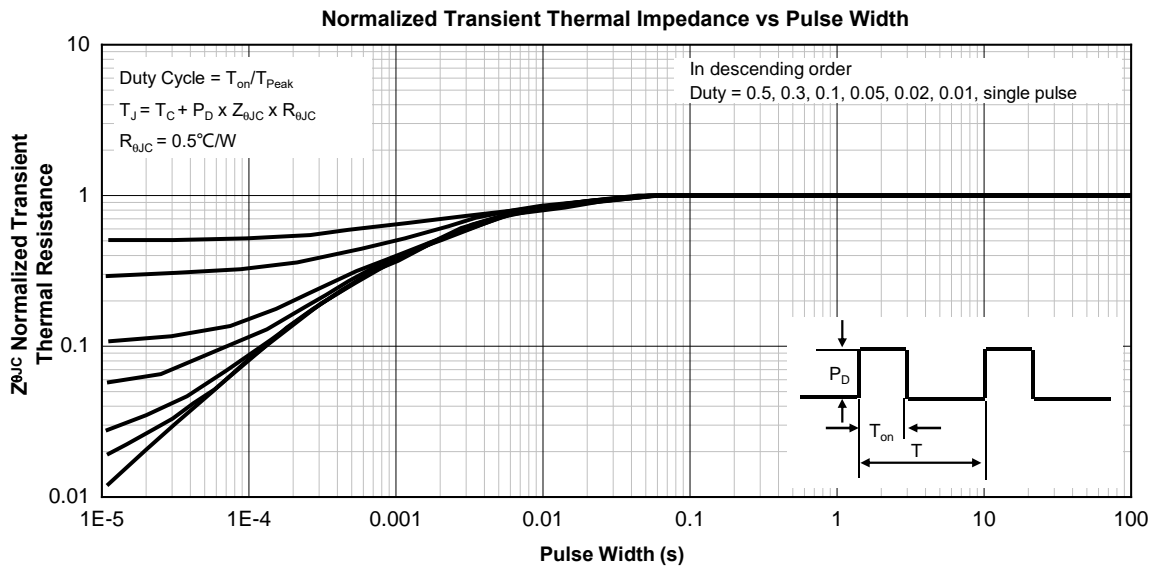
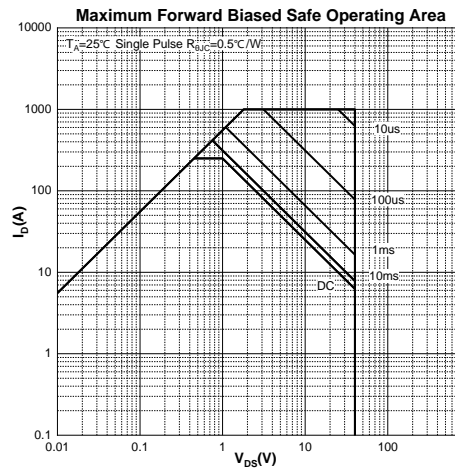
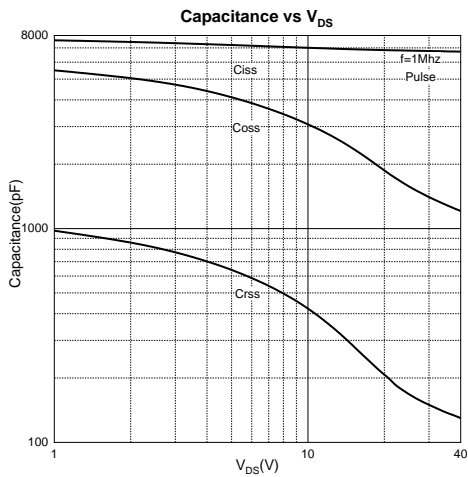
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	40			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 40V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 100$	nA
<b>On Characteristics<sup>4</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.0	1.8	3.0	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 50A$		1.2	1.6	m $\Omega$
		$V_{GS} = 4.5V, I_D = 50A$		1.7	2.5	
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 20V, V_{GS} = 0V, f = 1MHz$		6884		pF
Output Capacitance	$C_{oss}$			1827		
Reverse Transfer Capacitance	$C_{rss}$			182		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		3.9		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 20V, V_{GS} = 10V, I_D = 30A$		100		nC
Gate-source Charge	$Q_{gs}$			19		
Gate-drain Charge	$Q_{gd}$			15		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 20V, V_{GS} = 10V, I_D = 50A$ $R_G = 4\Omega$		15		ns
Turn-on Rise Time	$t_r$			8		
Turn-off Delay Time	$t_{d(off)}$			58		
Turn-off Fall Time	$t_f$			10		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>4</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 10A$			1.2	V

Notes :

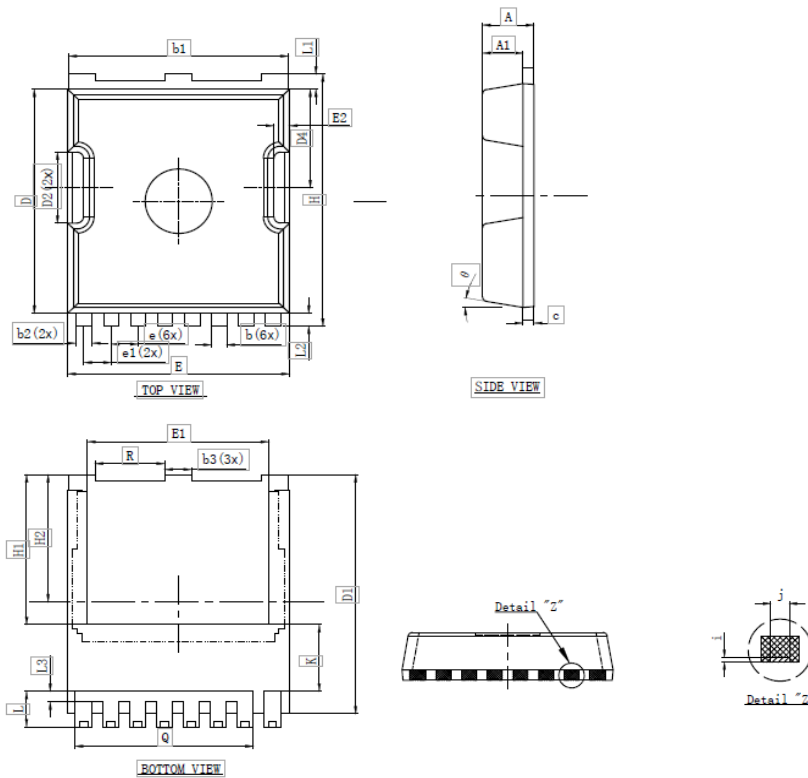
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.EAS condition:  $V_{DD} = 25V, V_{GS} = 10V, L = 0.3mH, R_G = 25\Omega$  Starting  $T_J = 25^\circ\text{C}$ .
- 4.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 5.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .And device mounted on a large heatsink
- 6.Device mounted on  $1in^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

## Typical Characteristics





## TOLL Package Information



SYMBOL	MILLIMETER		Dimensions In Inches	
	MIN.	MAX.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.700	1.900	0.067	0.075
b	0.600	0.800	0.024	0.031
b1	9.700	9.900	0.382	0.390
b2	0.650	0.850	0.026	0.033
b3	1.100	1.300	0.043	0.051
c	0.400	0.600	0.016	0.024
D	10.300	10.500	0.406	0.413
D1	11.000	11.200	0.433	0.441
D2	3.200	3.400	0.126	0.134
D4	4.470	4.670	0.176	0.184
E	9.800	10.000	0.386	0.394
E1	8.000	8.200	0.315	0.323
E2	0.500	0.700	0.020	0.028
e	1.200 BSC		0.047BSC	
e1	1.225 BSC		0.048BSC	
H	11.600	11.800	0.457	0.465
H1	6.950 BSC		0.247BSC	
H2	5.900 BSC		0.232BSC	
i	0.100 REF		0.004REF	
j	0.350 REF		0.014REF	
K	3.100 REF		0.122REF	
L	1.550	1.750	0.061	0.069
L1	0.600	0.800	0.024	0.031
L2	0.500	0.700	0.020	0.028
L3	0.400	0.600	0.016	0.024
Q	7.950 REF		0.313REF	
R	3.000	3.200	0.118	0.126
θ	10°			